

**【PP-05】**

## **Measurement of ion-induced secondary electron emission coefficient for MgO thin film with O<sub>2</sub> plasma treatment**

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The ion-induced secondary electron emission coefficient for MgO thin film with O<sub>2</sub> plasma treatment has been investigated by  $\gamma$ -FIB (focused ion beam) system. The MgO thin film deposited from sintered material with O<sub>2</sub> plasma treatment is found to have higher than that without O<sub>2</sub> plasma treatment. The energy of Ne<sup>+</sup> ions used has been ranged from 100eV to 200eV throughout this experiment. It is found that the highest secondary electron emission coefficient has been achieved for 10 minutes of O<sub>2</sub> plasma treatment.